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Substitute for form 1449A/B/PTO		Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	Not Yet Assigned
		Filing Date	Concurrently Herewith 10/03/2005
		First Named Inventor	Tomohiro Kawase
		Art Unit	1792
		Examiner Name	Not Yet Assigned- Hiteshev
Sheet	1	of	2
		Attorney Docket Number	20239/0202145-USO

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
	AA*	US-5,647,917-A	07-15-1997	Sumitomo Electric Industries, Ltd.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	†*
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			
	BA	JP-03-237088-A	10-22-1991	Nippon Mining Co Ltd	Abstract only	✓
	BB	JP-2000-313699-A	11-14-2000	Japan Energy Corp	Abstract only	✓
	BC	JP-03-040987-A	02-21-1991	Nippon Telegr & Teleph Corp <NTT>	Abstract only	✓
	BD	JP-08-078348-A	03-22-1996	Sumitomo Electric Ind Ltd	Abstract only	✓
	BE	JP-11-302094-A	11-02-1999	Japan Energy Corp	Abstract only	✓

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NON PATENT LITERATURE DOCUMENTS						
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T*
CA		International Search Report for PCT/JP2004/006427 mailed October 5, 2004				
CB		P. RUDOLPH, et al., Studies on interface curvature during vertical Bridgman growth of InP in a flat-bottom container, Journal of Crystal Growth, 1996, Vol. 158, pp 43-48				
CC		esp@cenet document view: Abstract of EP 0701008 published on March 13, 1996				
CD		XIAOYU HU, et al., Three Inch VGF Semi-insulating InP, Post Deadline Papers, Tenth International Conference on Indium Phosphide and Related Materials (IPRM '98), May 11-15, 1998, pp. 15-16				
CE		TOMOHIRO KAWASE, et al., Improvement of microscopic and macroscopic uniformity in 4-inch InP substrate for IC application by Vertical Boat Growth, GaAs IC Symposium, Technical Digest, October 20-23, 2002, pp. 147-150				
CF		T. ASAHII, et al., Growth of 100mm Diameter <100> InP Single Crystals by the Vertical Gradient Freezing Method, Post Deadline Papers, Tenth International Conference on Indium Phosphide and Related Materials (IPRM '98), May 11-15, 1998, pp. 1-2				
CG		TOSHIAKI ASAHII, et al., Growth of 100-mm-Diameter <100> InP Single Crystals by the Vertical Gradient Freezing Method, Jpn. J. Appl. Phys. Vol. 38, February, 1999, pp. 977-980				
CH		T. ASAHII, et al., VGF CRYSTAL GROWTH AND VAPOR-PHASE Fe DOPING TECHNOLOGIES FOR SEMI-INSULATING 100mm DIAMETER InP SUBSTRATES, 11th International Conference on Indium Phosphide and Related Materials, May 16-20, 1999, pp. 249-254				
CI		FUMIO MATSUMOTO, et al., Growth of twin-free <100> InP single crystals by the liquid encapsulated vertical Bridgman technique, Journal of Crystal Growth 132, 1998, pp. 348-350				
CJ		E.M. MONBERG, et al., THE DYNAMIC GRADIENT FREEZE GROWTH OF InP, Journal of Crystal Growth 94, 1989, pp. 109-114				
Examiner Signature	/Felisa Hiteshev/				Date Considered	03/20/2008

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Examiner Signature	/Felisa Hiteshew/	Date Considered	03/20/2008
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